

Silicon NPN Power Transistors

2SC2361

DESCRIPTION

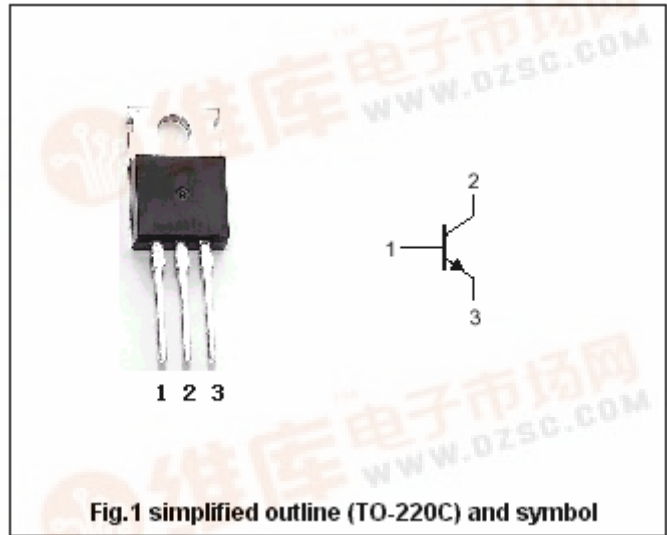
- With TO-220C package
- Complement to type 2SA1123
- Low collector saturation voltage

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	100	V
$V_{CEO}$	Collector-emitter voltage	Open base	70	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current (DC)		4	A
$P_C$	Collector dissipation	$T_C=25^\circ C$	25	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-50~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1 A; I <sub>B</sub> =0	70			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1m A; I <sub>C</sub> =0	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =0.4A			1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =3A; V <sub>CE</sub> =4V			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =100V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0			10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2.5A; V <sub>CE</sub> =3V	50		240	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A; V <sub>CE</sub> =10V		70		MHz

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PACKAGE OUTLINE

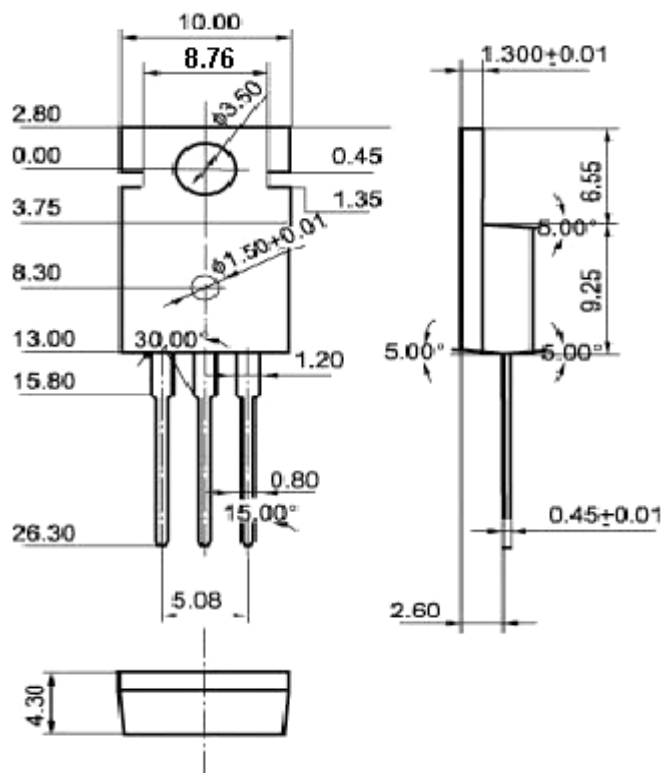


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$ mm)